

### **Amendments to the Claims**

This listing of claim will replace all prior versions and listings of claim in the application. Please cancel claims 1, 6, and 12. Please add new claims 17, 18, and 19. Please amend claims 2, 7, and 13.

1. (Cancelled)
2. (Currently amended) The method of claim ~~1~~ 17 wherein the temperature is between about 450 and about 480 degrees Celsius.
3. (Original) The method of claim 2 wherein pressure is between about 200 mTorr and about 1 Torr.
4. (Original) The method of claim 3 wherein an inert gas is flowed over the surface with the  $\text{SiH}_4$  and  $\text{BCl}_3$ .
5. (Original) The method of claim 4 wherein the inert gas is helium.
6. (Cancelled)
7. (Currently amended) The method of claim ~~6~~ 18, wherein the second source gas comprises about 0.1 percent  $\text{BCl}_3$  or more.
8. (Original) The method of claim 7, wherein the second source gas further comprises an inert gas.
9. (Original) The method of claim 8, wherein the temperature is between about 450 and about 480 degrees Celsius.

10. (Original) The method of claim 9, wherein the inert gas is helium.
11. (Original) The method of claim 8, wherein the pressure is between about 200 mTorr and about 1 Torr.
12. (Cancelled)
13. (Currently amended) The method of claim ~~12~~ 19 wherein the step of depositing the polysilicon film comprises substantially simultaneously flowing  $\text{SiH}_4$  and  $\text{BCl}_3$  over the surface.
14. (Original) The method of claim 13 wherein an average concentration of boron atoms in the polysilicon is between about  $7 \times 10^{20}$  and about  $3 \times 10^{21}$  per cubic centimeter.
15. (Original) The method of claim 14 wherein the temperature is between about 450 and about 480 degrees Celsius.
16. (Original) The method of claim 15 wherein the pressure is between 200 mTorr and 1 Torr.
17. (New) A method for depositing a doped polysilicon film comprising:
  - providing a surface; and
  - substantially simultaneously flowing  $\text{SiH}_4$  and  $\text{BCl}_3$  over the surface at a temperature less than or equal to about 500 degrees Celsius under conditions that achieve an average concentration in the doped polysilicon film of between about  $7 \times 10^{20}$  and about  $3 \times 10^{21}$  boron atoms per cubic centimeter, wherein the doped polysilicon film is polycrystalline as deposited.
18. (New) A method for forming an in-situ doped polysilicon film, the method comprising:
  - providing a surface; and

substantially simultaneously flowing a first source gas comprising  $\text{SiH}_4$  and a second source gas comprising  $\text{BCl}_3$  over the surface at a temperature less than about 500 degrees Celsius under conditions sufficient to achieve in the doped polysilicon an average concentration of between about  $7 \times 10^{20}$  and about  $3 \times 10^{21}$  boron atoms per cubic centimeter, wherein during this flowing step, polycrystalline silicon is deposited.

19. (New) A method for depositing an in-situ doped polysilicon film comprising:
- providing a substrate comprising a substantially horizontal surface and a substantially vertical sidewall descending from the horizontal surface, the sidewall having a top; and
  - depositing the in-situ doped polysilicon film on the surface at a temperature less than about 500 degrees Celsius, wherein:
    - a first thickness of the film at its thinnest point on the vertical sidewall is at least 80 percent of a second thickness of the film on the sidewall at the top of the sidewall, and
    - a third thickness of the film on the horizontal surface is at least 200 angstroms, and wherein, during the depositing step, doped polycrystalline silicon is deposited.